AMENDMENTS TO THE SPECIFICATION

Please delete the section heading "Summary of the Invention" on page 3.

Please delete the first, second, third, fourth, fifth, sixth, and seventh paragraphs on page 6 (which were added in the last amendment).

Please amend the first full paragraph on page 7 as follows:

Figure 5 further shows a silicided refractory metal layer 80 which, in this case, is a Cobalt silicide layer. In practice, Cobalt or another refractory metal is blanket deposited on the device and thereafter reacted at elevated temperatures with the silicon to form the silicide. The unreacted Cobalt or other refractory metal is then etched off leaving only the areas of Cobalt silicide on the polysilicon areas. The silicide at this point in the process is often referred to as salicide. As can be seen in Figure 5, the Cobalt silicide layer is formed on top of the first and second polysilicon layers but does not extend over the oxide dielectric 82. In this way oxide dielectric 82 prevents the Cobalt silicide from shorting out the p-n junction prematurely. As can be seen, the regions 62 and 68 are also isolated from the second polysilicon region 56 by the nitride spacers 84. However, a low resistance path is facilitated by n+ region 58. Thus, when the device is reverse biased by applying a voltage across the contacts 90, which in this embodiment comprise aluminum contacts formed in titanium nitride (TiN) sleeves 94, a fusing current is established which heats the p-n junction and causes the Cobalt silicide to migrate across the p-n junction to form a silicide bridge, in this case a Cobalt silicide bridge. Thus, by using standard process steps in a double poly process and modifying the resistance path across n-epitaxial or ~~n-sinker~~ n+ sinker region 52, Cobalt or another refractory metal can be used to establish a silicide bridge across the p-n junction thereby effectively shorting out the

p-n junction. Thus, the present invention allows the device to be used as a zener zap diode.